

CMHD2003

SURFACE MOUNT
HIGH VOLTAGE SILICON
SWITCHING DIODE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMHD2003 is a Silicon Switching Diode, manufactured by the epitaxial planar process, epoxy molded in a SOD-123 surface mount package, designed for applications requiring high voltage capability.

MARKING CODE: C03



SOD-123 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL	UNITS
Continuous Reverse Voltage	V_R	V
Continuous Forward Current	I_F	mA
Average Rectified Current	I_O	mA
Peak Repetitive Forward Current	I_{FRM}	mA
Peak Forward Surge Current, $t_p < 1.0\text{s}$ ($T_C=25^\circ\text{C}$)	I_{FSM}	A
Power Dissipation	P_D	mW
Operating and Storage Junction Temperature	T_J, T_{Stg}	${}^\circ\text{C}$
Thermal Resistance	Θ_{JA}	${}^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

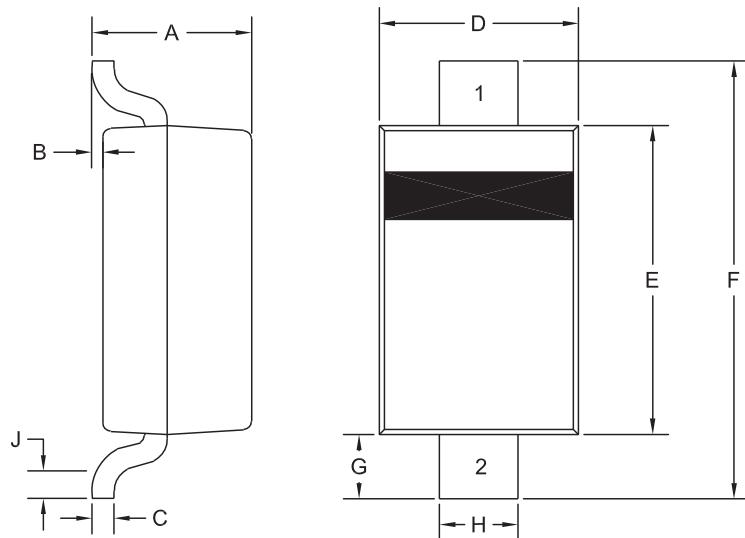
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=200\text{V}$			100	nA
I_R	$V_R=200\text{V}, T_C=100^\circ\text{C}$			15	μA
V_F	$I_F=100\text{mA}$			1.0	V
C_T	$V_R=0, f=1.0\text{MHz}$		1.5		pF
t_{tr}	$I_F=I_R=30\text{mA}, R_L=100\Omega$, Rec. to 3.0mA			50	ns

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SOD-123 CASE - MECHANICAL OUTLINE



R5

LEAD CODE

- 1) Cathode
- 2) Anode

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SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	0.000	0.005	0.00	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.110	2.50	2.80
F	0.142	0.154	3.60	3.90
G	0.016	-	0.40	-
H	0.020	0.028	0.50	0.70
J	0.010	-	0.25	-

SOD-123 (REV:R5)

R5 (5-August 2010)